



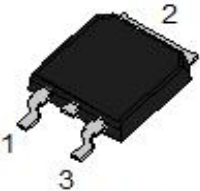
# B772M

## TRANSISTOR (PNP)

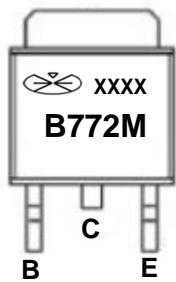
### FEATURES

- Low Speed Switching
- Collector Current:  $I_c = -3.0A$

**Package**

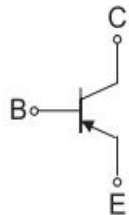


TO-252



B:BASE  
C:COLLECTOR  
E:EMITTER

Equivalent Circuit



### Package Marking and Ordering Information

Product ID	PACK	Qty (pcs)
B772M	TO-252	2500

### MAXIMUM RATINGS( $T_a = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
VCBO	Collector-Base-Voltage	-40	V
VCEO	Collector-Emitter Voltage	-30	V
VEBO	Emitter-Base Voltage	-6	V
IC	Collector Current	-3	A
PC	Collector Power Dissipation	1.25	W
R $\theta$ JA	Thermal Resistance From Junction To Ambient	100	$^\circ C/W$
Tj	Junction Temperature	-55+150	$^\circ C$
Tstg	Storage Temperature		



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## TRANSISTOR (PNP)

### ELECTEICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

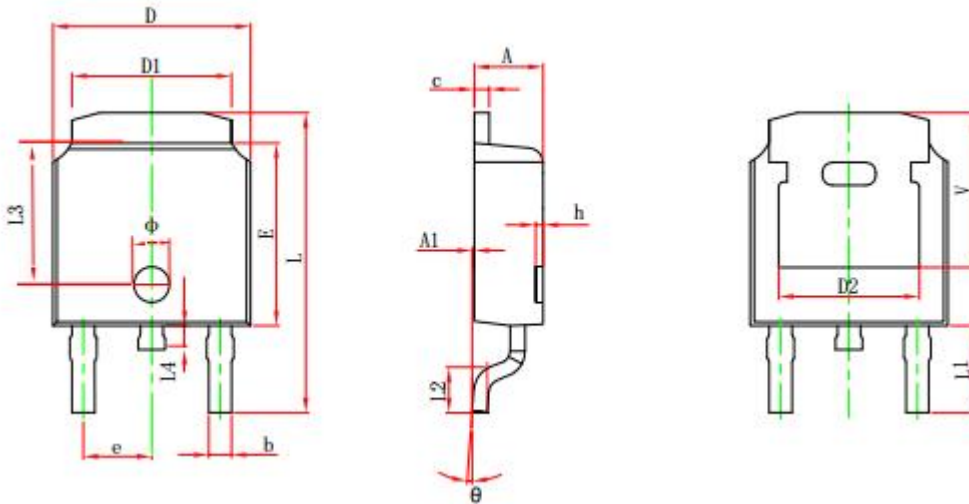
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$			-1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-30V, I_B=0$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-6V, I_C=0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-2V, I_C=-1A$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.2	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-0.1A, f=10MHz$	50	80		MHz

### CLASSIFICATION OF $h_{FE}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

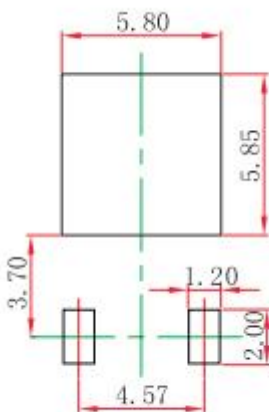


### TO-252-2L Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	4.460 REF.		0.1756 REF.	
L4	0.600	1.000	0.024	0.039
Phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

### TO-252-2L Suggested Pad Layout



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

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